## Designing crystallization in phase-change materials for neuro-inspired computing

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**Citation Report** 

#	Article	IF	CITATIONS
1	Computational phase-change memory: beyond von Neumann computing. Journal Physics D: Applied Physics, 2019, 52, 443002.	1.3	78
2	Effect of Cu doping on microstructure and thermal stability of Ge2Sb2Te5 thin film. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	1.1	8
3	Phase-change heterostructure enables ultralow noise and drift for memory operation. Science, 2019, 366, 210-215.	6.0	261
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7	Effects of biaxial strain on interfacial intermixing and local structures in strain engineered GeTe-Sb2Te3 superlattices. Applied Surface Science, 2019, 493, 904-912.	3.1	11
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20	Ovonic threshold switching selectors for three-dimensional stackable phase-change memory. MRS Bulletin, 2019, 44, 715-720.	1.7	70
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